

# BC846PN/UPN\_BC847PN

**Maximum Ratings** 

Parameter	Symbol	Value	Unit
Collector-emitter voltage	V <sub>CEO</sub>		V
BC846PN/UPN		65	
BC847PN		45	
Collector-emitter voltage	V <sub>CES</sub>		
BC846PN/UPN		80	
BC847PN		50	
Collector-base voltage	V <sub>CBO</sub>		
BC846PN/UPN		80	
BC847PN		50	
Emitter-base voltage	V <sub>EBO</sub>	6	
Collector current	I <sub>C</sub>	100	mA
Peak collector current, $t_p \le 10 \text{ ms}$	/ <sub>CM</sub>	200	
Total power dissipation-	P <sub>tot</sub>		mW
<i>T</i> <sub>S</sub> ≤ 115°C, BC846PN, BC847PN		250	
<i>T</i> <sub>S</sub> ≤ 118°C, BC846UPN		250	
Junction temperature	$T_{ m j}$	150	°C
Storage temperature	T <sub>stg</sub>	-65 150	

# **Thermal Resistance**

Parameter	Symbol	Value	Unit
Junction - soldering point <sup>1)</sup>	R <sub>thJS</sub>		K/W
BC846PN, BC847PN		≤ 140	
BC846UPN		≤ 130	

 $<sup>^{1}</sup>$ For calculation of  $R_{thJA}$  please refer to Application Note AN077 (Thermal Resistance Calculation)



# BC846PN/UPN\_BC847PN

**Electrical Characteristics** at  $T_A = 25$ °C, unless otherwise specified **Symbol Values** Unit **Parameter** min. typ. max. **DC Characteristics**  $V_{(BR)CEO}$ ٧ Collector-emitter breakdown voltage  $I_{\rm C}$  = 10 mA,  $I_{\rm B}$  = 0 , BC846PN/UPN 65  $I_{\rm C}$  = 10 mA,  $I_{\rm B}$  = 0 , BC847PN 45  $V_{(BR)CBO}$ Collector-base breakdown voltage  $I_{\rm C}$  = 10  $\mu$ A,  $I_{\rm F}$  = 0 , BC846PN/UPN 80  $I_{\rm C} = 10 \, \mu \text{A}, I_{\rm F} = 0 \, , \, \text{BC847PN}$ 50 Collector-emitter breakdown voltage  $V_{(BR)CES}$  $I_{\rm C}$  = 10  $\mu$ A,  $V_{\rm BE}$  = 0 , BC846PN/UPN 80  $I_{\rm C}$  = 10  $\mu$ A,  $V_{\rm BE}$  = 0 , BC847PN 50 Emitter-base breakdown voltage  $V_{(BR)EBO}$ 6  $I_{\rm F} = 1 \, \mu A, I_{\rm C} = 0$ Collector-base cutoff current μΑ  $I_{CBO}$  $V_{\rm CB} = 50 \text{ V}, I_{\rm F} = 0$ 0.015  $V_{\rm CB} = 30 \text{ V}, I_{\rm E} = 0 , T_{\rm A} = 150 \,^{\circ}{\rm C}$ 5 DC current gain $h_{\mathsf{FE}}$  $I_{\rm C} = 10 \, \mu \text{A}, \, V_{\rm CF} = 5 \, \text{V}$ 250  $I_{\rm C}$  = 2 mA,  $V_{\rm CE}$  = 5 V 200 290 450 Collector-emitter saturation voltage<sup>1)</sup>  $V_{\mathsf{CEsat}}$ mV  $I_{\rm C}$  = 10 mA,  $I_{\rm B}$  = 0.5 mA 300 90  $I_{\rm C}$  = 100 mA,  $I_{\rm B}$  = 5 mA 200 650 Base emitter saturation voltage-1)  $V_{\mathsf{BEsat}}$  $I_{\rm C}$  = 10 mA,  $I_{\rm B}$  = 0.5 mA 700  $I_{\rm C}$  = 100 mA,  $I_{\rm B}$  = 5 mA 900 Base-emitter voltage-1)  $V_{\rm BE(ON)}$ 

3

 $I_{\rm C}$  = 2 mA,  $V_{\rm CF}$  = 5 V

 $I_{\rm C}$  = 10 mA,  $V_{\rm CE}$  = 5 V

580

660

750

<sup>&</sup>lt;sup>1</sup>Pulse test: t 300 $\mu$ s, D = 2%



# BC846PN/UPN\_BC847PN

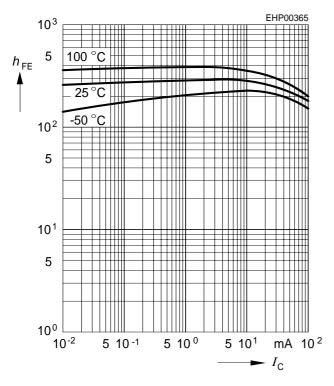
**Electrical Characteristics** at  $T_A = 25$ °C, unless otherwise specified

Parameter	Symbol	Values			Unit
		min.	typ.	max.	1
AC Characteristics					
Transition frequency	$f_{T}$	-	250	-	MHz
$I_{\rm C}$ = 10 mA, $V_{\rm CE}$ = 5 V, $f$ = 100 MHz					
Collector-base capacitance	C <sub>cb</sub>	-	1.5	-	pF
$V_{CB} = 10 \text{ V}, f = 1 \text{ MHz}$					
Emitter-base capacitance	C <sub>eb</sub>	-	8	-	
$V_{\text{EB}} = 0.5 \text{ V}, f = 1 \text{ MHz}$					
Short-circuit input impedance	h <sub>11e</sub>	-	4.5	-	kΩ
$I_{\rm C}$ = 2 mA, $V_{\rm CE}$ = 5 V, $f$ = 1 kHz					
Open-circuit reverse voltage transf. ratio	h <sub>12e</sub>	-	2	-	10-4
$I_{\rm C}$ = 2 mA, $V_{\rm CE}$ = 5 V, $f$ = 1 kHz					
Short-circuit forward current transf. ratio	h <sub>21e</sub>	-	330	-	-
$I_{\rm C}$ = 2 mA, $V_{\rm CE}$ = 5 V, $f$ = 1 kHz					
Open-circuit output admittance	h <sub>22e</sub>	-	30	-	μS
$I_{\rm C}$ = 2 mA, $V_{\rm CE}$ = 5 V, $f$ = 1 kHz					



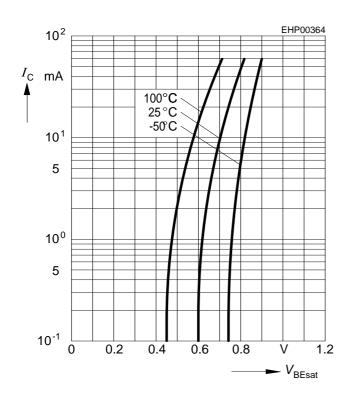
# **DC** current gain $h_{FE} = f(I_C)$

$$V_{CE} = 5 \text{ V}$$



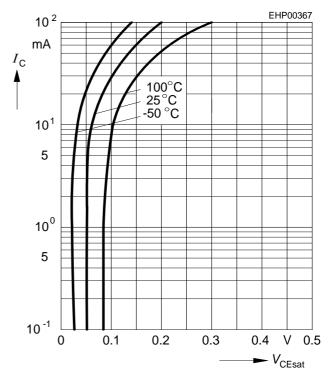
#### **Base-emitter saturation voltage**

$$I_{\rm C} = f(V_{\rm BEsat}), h_{\rm FE} = 20$$



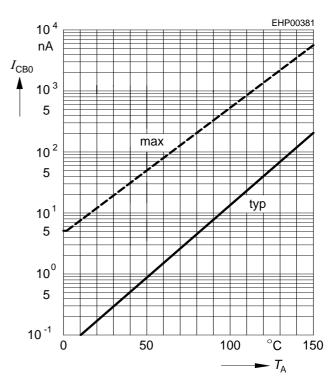
#### Collector-emitter saturation voltage

$$I_{\text{C}} = f(V_{\text{CEsat}}), h_{\text{FE}} = 20$$



# Collector cutoff current $I_{CBO} = f(T_A)$

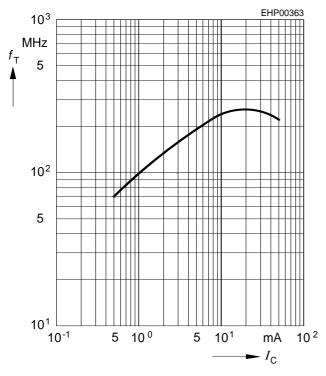
$$V_{\rm CBO}$$
 = 30 V



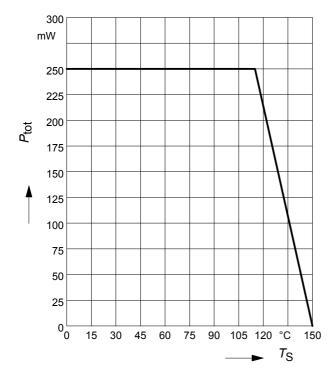




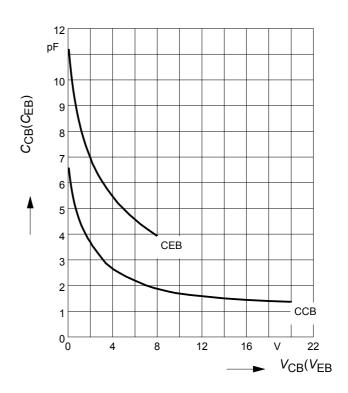
Transition frequency  $f_T = f(I_C)$  $V_{CE} = 5 \text{ V}, f = 100 \text{ MHz}$ 



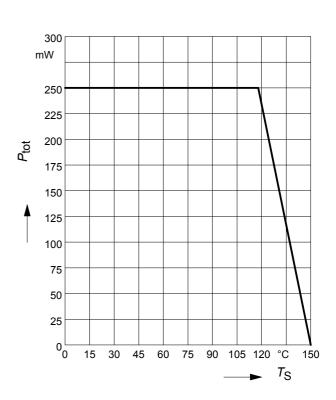
Total power dissipation  $P_{tot} = f(T_S)$  BC846PN, BC847PN



Collector-base capacitance  $C_{cb} = f(V_{CB})$ Emitter-base capacitance  $C_{eb} = f(V_{EB})$ 

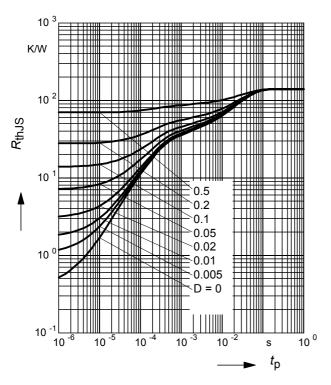


Total power dissipation  $P_{tot} = f(T_S)$ BC846UPN

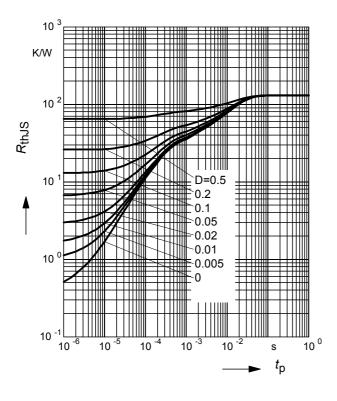




# Permissible Pulse Load $R_{thJS} = f(t_p)$ BC846PN, BC847PN

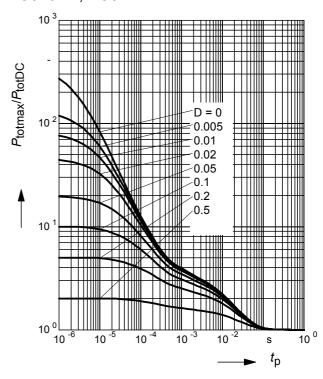


**Permissible Puls Load**  $R_{thJS} = f(t_p)$  BC846UPN



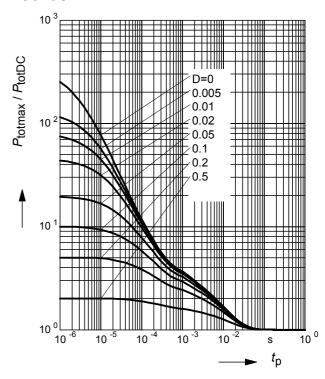
#### **Permissible Pulse Load**

 $P_{\text{totmax}}/P_{\text{totDC}} = f(t_{\text{p}})$ BC846PN, BC847PN



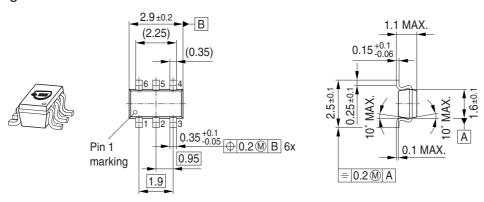
#### **Permissible Pulse Load**

 $P_{\text{totmax}}/P_{\text{totDC}} = f(t_{\text{p}})$ BC846UPN

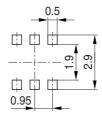




## Package Outline

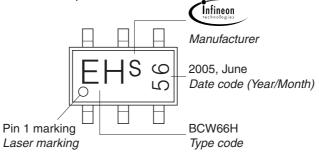


#### Foot Print



# Marking Layout (Example)

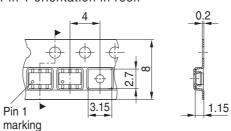
Small variations in positioning of Date code, Type code and Manufacture are possible.



# Standard Packing

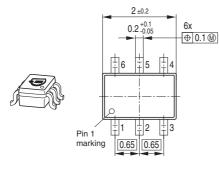
Reel ø180 mm = 3.000 Pieces/Reel Reel ø330 mm = 10.000 Pieces/Reel

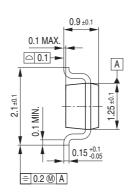
For symmetric types no defined Pin 1 orientation in reel.



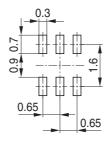


## Package Outline



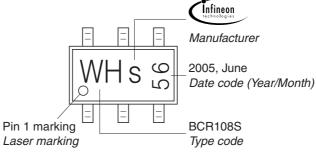


#### Foot Print



# Marking Layout (Example)

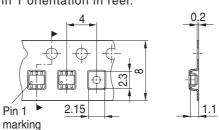
Small variations in positioning of Date code, Type code and Manufacture are possible.



# Standard Packing

Reel ø180 mm = 3.000 Pieces/Reel Reel ø330 mm = 10.000 Pieces/Reel

For symmetric types no defined Pin 1 orientation in reel.





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